

Patent Application
10/010,162

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Fwu-Iuan Ilshieh et al.
Serial No.: 10/010,162
Filed: November 20, 2001
Title: Method Of Forming Narrow Trenches In Semiconductor Substrates
Art Unit: 2812
Examiner: Angel Roman
Docket No.: GS 149
Commissioner for Patents
PO Box 1450
Alexandria, VA 22313-1450

RECEIVED
CENTRAL FAX CENTER

MAY 31 2005

PETITION UNDER 37 CFR 1.136(a) and RESPONSE TO FINAL OFFICE ACTION

Applicants hereby petition the Assistant Commissioner to grant a one month extension of time, up to and including Tuesday, May 31, 2005 (May 28, 2005, being a Saturday, and Monday, May 30, 2005 being a Federal Holiday), in which to respond to the Office Action dated January 28, 2005 in the above-identified application. The extension fee may be charged to deposit account No. 50-1047. In addition, any deficiencies may be charged to deposit account No. 50-1047.

In response to the Office Action dated January 28, 2005, the period therefore having been extended by a Petition therefore and payment of the extension fee, kindly consider the following remarks.

Certificate of Facsimile Transmission

I hereby certify that this document and any document referenced herein has been transmitted via facsimile to the U.S. Patent and Trademark Office at (703) 872-9306 on May 31, 2005.

Karin L. Williams, Reg. No. 36,721

(Printed Name of Person Mailing Correspondence)

Karin L. Williams
(Signature)

05/14/2005 DSASFAT 00000001 501047 10010162
Sale Ref: 00000001 DAN: 501047 10010162
01 FC:1251 120.00 DA